

74VHC00 • 74VHCT00 Quad 2-Input NAND Gate

General Description

The VHC/VHCT00 is an advanced high-speed CMOS 2-Input NAND Gate fabricated with silicon gate CMOS technology. It achieves the high-speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 3 stages, including buffer output, which provide high noise immunity and stable output. An input protection circuit insures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery backup. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High Speed: VHC t_{pd} = 3.7ns (typ) at T_A = 25°C VHCT t_{pd} = 5.0 ns (typ) at T_A = 25°C
- High noise immunity:

 VHC V_{NIH} = V_{NIL} = 28% V_{CC} (min)

 VHCT V_{IH} = 2.0V, V_{IL} = 0.8V
- Power down protection: VHC inputs only
- VHCT inputs and outputs
- Low noise: V_{OLP} = 0.8V (max)
- Low power dissipation: I_{CC} = 2 µA (max) at T_A = 25°C
- Pin and function compatible with 74HC/HCT00

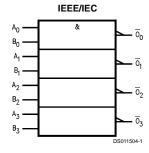
 NOTE: ADD EXTERNAL PULL UP RESISTOR TO
 VHCT OUTPUTS TO DRIVE CMOS INPUTS

Ordering Code:

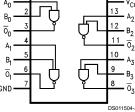
Commercial	Package Number	Package Description
74VHC00M	M14A	14-Lead Molded JEDEC SOIC
74VHC00SJ	M14D	14-Lead Molded EIAJ SOIC
74VHC00MTC	MTC14	14-Lead Molded JEDEC Type 1 TSSOP
74VHC00N	N14A	14-Lead Molded DIP
74VHCT00M	M14A	14-Lead Molded JEDEC SOIC
74VHCT00SJ	M14D	14-Lead Molded EIAJ SOIC
74VHCT00MTC	MTC14	14-Lead Molded JEDEC Type 1 TSSOP
74VHCT00N	N14A	14-Lead Molded DIP

Surface mount packages are also available on Tape and Reel. Specify by appending the suffix letter "X' to the ordering code.

Logic Symbol



Connection Diagram



Pin Descriptions

Pin Names	Description
An, Bn	Inputs
On	Outputs

Truth Table

Α	В	0
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

Absolute Maximum Ratings (Note 1)

 $\begin{array}{lll} \mbox{Supply Voltage (V}_{\mbox{\scriptsize CC}}) & -0.5\mbox{\scriptsize V to +7.0V} \\ \mbox{\scriptsize DC Input Voltage (V}_{\mbox{\scriptsize IN}}) & -0.5\mbox{\scriptsize V to +7.0V} \\ \end{array}$

DC Output Voltage (V_{OUT})

 $\begin{array}{ccc} \text{VHC} & -0.5 \text{V to V}_{\text{CC}} + 0.5 \text{V} \\ \text{VHCT (Note 2)} & -0.5 \text{V to 7.0V} \\ \text{Input Diode Current (I}_{\text{IK}}) & -20 \text{ mA} \end{array}$

Output Diode Current (I_{OK})

 $\begin{array}{ccc} \text{VHC} & \pm 20 \text{ mA} \\ \text{VHCT} & -20 \text{ mA} \\ \text{DC Output Current (I}_{\text{OUT}}) & \pm 25 \text{ mA} \\ \text{DC V}_{\text{CC}}/\text{GND Current (I}_{\text{CC}}) & \pm 50 \text{ mA} \\ \text{Storage Temperature (T}_{\text{STG}}) & -65 ^{\circ}\text{C to } +150 ^{\circ}\text{C} \\ \end{array}$

Lead Temperature (T_L)

(Soldering, 10 seconds) 260°C

Recommended Operating Conditions (Note 3)

Supply Voltage (V_{CC})

 $\begin{array}{ccc} \text{VHC} & 2.0 \text{V to } +5.5 \text{V} \\ \text{VHCT} & 4.5 \text{V to } 5.5 \text{V} \\ \text{Input Voltage } (\text{V}_{\text{IN}}) & 0 \text{V to } +5.5 \text{V} \\ \text{Output Voltage } (\text{V}_{\text{OUT}}) & 0 \text{V to } \text{V}_{\text{CC}} \\ \text{Operating Temperature } (\text{T}_{\text{OPR}}) & -40 ^{\circ} \text{C to } +85 ^{\circ} \text{C} \\ \end{array}$

Input Rise and Fall Time (t_r, t_f)

 $\label{eq:Vcc} \begin{array}{ll} \mbox{V}_{\mbox{CC}} = 3.3 \mbox{V} \ \pm 0.3 \mbox{V} \ (\mbox{VHC Only}) & 0 \ \mbox{ns/V} \ \sim \ 100 \ \mbox{ns/V} \\ \mbox{V}_{\mbox{CC}} = 5.0 \mbox{V} \ \pm 0.5 \mbox{V} & 0 \ \mbox{ns/V} \ \sim \ 20 \ \mbox{ns/V} \end{array}$

Note 1: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. Fair-child does not recommend operation outside databook specifications.

Note 2: $V_{OUT} > V_{CC}$ only if output is in H state.

Note 3: Unused inputs must be held HIGH or LOW. They may not float.

DC Electrical Characteristics for VHC

Symbol	Parameter	V _{CC}		T _A = 25°(:		-40°C	Units	Conditions			
		(V)				to +85°C		to +85°C				
			Min	Тур	Max	Min	Max					
V _{IH}	High Level Input	2.0	1.50			1.50		V				
	Voltage	3.0-5.5	0.7 V _{CC}			0.7 V _{CC}		\ \				
V _{IL}	Low Level Input	2.0			0.50		0.50	V				
	Voltage	3.0–5.5 0.3 V _{CC} 0.3 V _{CC}	\ \									
V _{OH}	High Level Output	2.0	1.9	2.0		1.9			V _{IN} = V _{IH}	I _{OH} = -50 μA		
	Voltage	3.0	2.9	3.0		2.9		V	or V _{IL}			
		4.5	4.4	4.5		4.4						
		3.0	2.58			2.48		V		$I_{OH} = -4mA$		
		4.5	3.94			3.80		\ \ \		$I_{OH} = -8mA$		
V _{OL}	Low Level Output	2.0		0.0	0.1		0.1		V _{IN} = V _{IH}	I _{OL} = 50 μA		
	Voltage	3.0		0.0	0.1		0.1	V	or V _{IL}			
		4.5		0.0	0.1		0.1					
		3.0			0.36		0.44	V		I _{OL} = 4 mA		
		4.5			0.36		0.44	\ \ \		I_{OL} = 8 mA		
I _{IN}	Input Leakage			•	•				V _{IN} = 5.5V or	GND		
	Current	0-5.5			±0.1		±1.0	μΑ				
lcc	Quiescent Supply				•				V _{IN} = V _{CC} or	GND		
	Current	5.5			2.0		20.0	μΑ				

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Noise Characteristics for VHC

Symbol	Parameter	V _{CC}	T _A = 25°C		Units	Conditions	
		(V)	Тур	Limit			
V _{OLP}	Quiet Output Maximum	5.0	0.3	0.8	V	C _L = 50 pF	
(Note 4)	Dynamic V _{OL}						
V _{OLV}	Quiet Output Minimum	5.0	-0.3	-0.8	V	C _L = 50 pF	
(Note 4)	Dynamic V _{OL}						
V _{IHD}	Minimum High Level	5.0		3.5	V	C _L = 50 pF	
(Note 4)	Dynamic Input Voltage						
V _{ILD}	Maximum Low Level	5.0		1.5	V	C _L = 50 pF	
(Note 4)	Dynamic Input Voltage						

Note 4: Parameter guaranteed by design

AC Electrical Characteristics for VHC

Symbol	Parameter	V _{CC} (V)	T _A = 25°C				–40°C 85°C	Units	Conditions
			Min	Тур	Max	Min	Max		
t _{PLH} ,	Propagation	3.3 ±0.3		5.5	7.9	1.0	9.5	ns	C _L = 15 pF
t _{PHL}	Delay			8.0	11.4	1.0	13.0		C _L = 50 pF
		5.0 ±0.5		3.7	5.5	1.0	6.5	ns	C _L = 15 pF
				5.2	7.5	1.0	8.5		C _L = 50 pF
C _{IN}	Input Capacitance			4	10		10	pF	V _{CC} = Open
C _{PD}	Power Dissipation			19				pF	(Note 5)
	Capacitance								

Note 5: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained from the equation: I_{CC} (opr.) = C_{PD} * V_{CC} * f_{IN} + $I_{CC}/4$ (per gate).

DC Electrical Characteristics for VHCT

Symbol	Parameter	V _{cc}	-	Γ _A = 25°0	3	T _A = -40°C		Units	Co	nditions
		(V)				to +	to +85°C			
			Min	Тур	Max	Min	Max			
V _{IH}	High Level Input Voltage	4.5	2.0			2.0		V		
		5.5	2.0			2.0		\ \ \		
V _{IL}	Low Level Input Voltage	4.5			0.8		0.8	V		
		5.5			0.8		0.8	\ \ \		
V _{OH}	High Level Output Voltage	4.5	3.15	3.65		3.15		V	V _{IN} = V _{IH}	I _{OH} = -50 μA
		4.5	2.5			2.4		V		I _{OH} = -8 mA
V _{OL}	Low Level Output Voltage	4.5		0.0	0.1		0.1	V	V _{IN} = V _{IH}	I _{OL} = 50 μA
		4.5			0.36		0.44	V		I _{OL} = 8 mA
I _{IN}	Input Leakage Current	0-5.5			±0.1		±1.0	μA	V _{IN} = 5.5V or	GND
I _{CC}	Quiescent Supply Current	5.5			2.0		20.0	μA	V _{IN} = V _{CC} or C	GND
I _{CCT}	Maximum I _{CC} / Input	5.5			1.35		1.50	mA	V _{IN} = 3.4V Other Inputs = V _{CC} or GND	
I _{OFF}	Output Leakage Current (Power Down State)	0.0			0.5		5.0	μА	V _{OUT} = 5.5V	

Noise Characteristics for VHCT

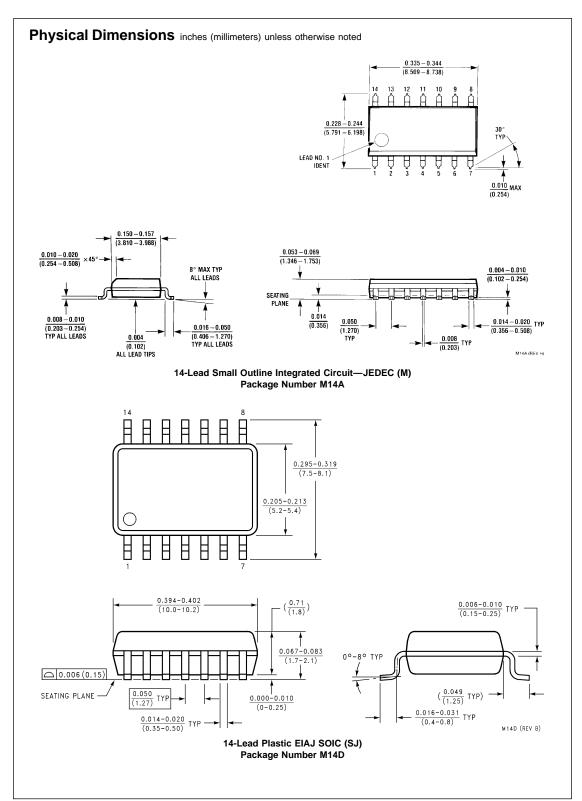
Symbol	Parameter	V _{cc}	T _A = 25°C		Units	Conditions
		(V)	Тур	Limit		
V _{OLP} (Note 6)	Quiet Output Maximum Dynamic V _{OL}	5.0	0.4	0.8	V	C _L = 50 pF
V _{OLV} (Note 6)	Quiet Output Minimum Dynamic V _{OL}	5.0	-0.4	-0.8	V	C _L = 50 pF
V _{IHD} (Note 6)	Minimum High Level Dynamic Input Voltage	5.0		2.0	V	C _L = 50 pF
V _{ILD} (Note 6)	Maximum Low Level Dynamic Input Voltage	5.0		0.8	V	C _L = 50 pF

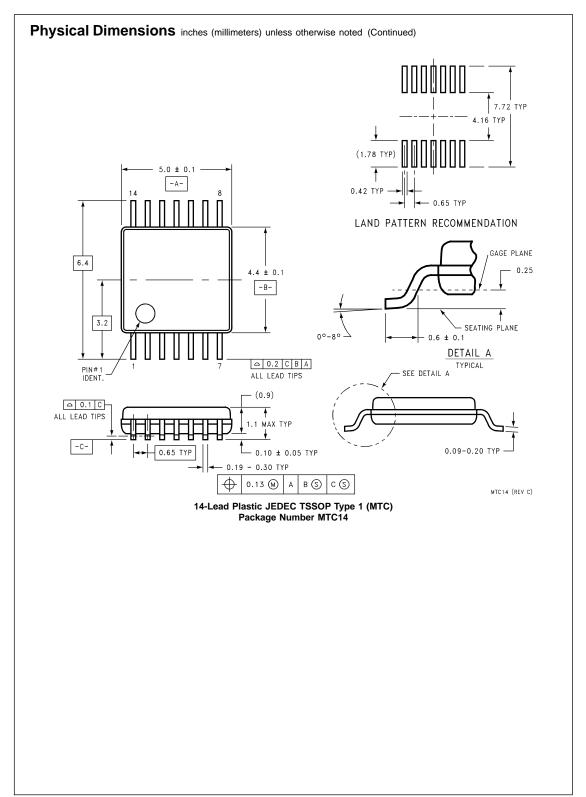
Note 6: Parameter guaranteed by design.

AC Electrical Characteristics for VHCT

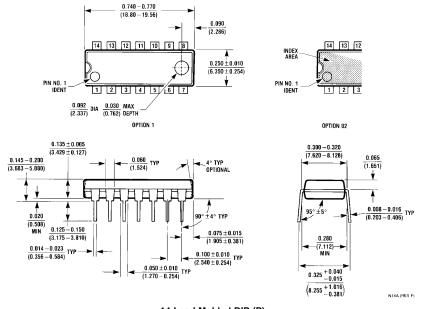
Symbol	Parameter	V _{cc}	T _A = 25°C		T _A = -40°C		Units	Conditions	Fig.	
		(V)			to +85°C				No.	
			Min	Тур	Max	Min	Max	1		
t _{PLH}	Propagation Delay	5.0		5.0	6.9	1.0	8.0	ns	C _L = 15 pF	
t _{PHL}		±0.5		5.5	7.9	1.0	9.0]	C _L = 50 pF	
C _{IN}	Input Capacitance			4	10		10	pF	V _{CC} = Open	
C _{PD}	Power Dissipation			17				pF	(Note 7)	
	Capacitance									

Note 7: C_{PD} is defined as the value of the internal equivalent capacitance, which is calculated from the operating current consumption without load. Average operating current can be obtained from the equation: I_{CC} (opr.) = C_{PD} * V_{CC} * I_{IN} + I_{CC} /4 (per gate)





Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



14-Lead Molded DIP (P) Package Number N14A

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